

2SK1835

Silicon N Channel MOS FET

REJ03G0978-0400 Rev.4.00 Jun 04, 2008

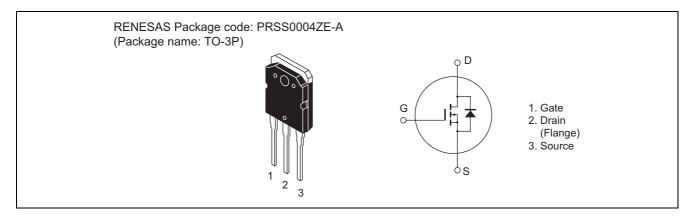
Application

High speed power switching

Features

- High breakdown voltage ($V_{DSS} = 1500 \text{ V}$)
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switching regulator

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	1500	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I _D	4	А
Drain peak current	I _{D(pulse)} Note1	10	А
Body to drain diode reverse drain current	I _{DR}	4	А
Channel dissipation	Pch Note2	125	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1 %

2. Value at $Tc = 25^{\circ}C$

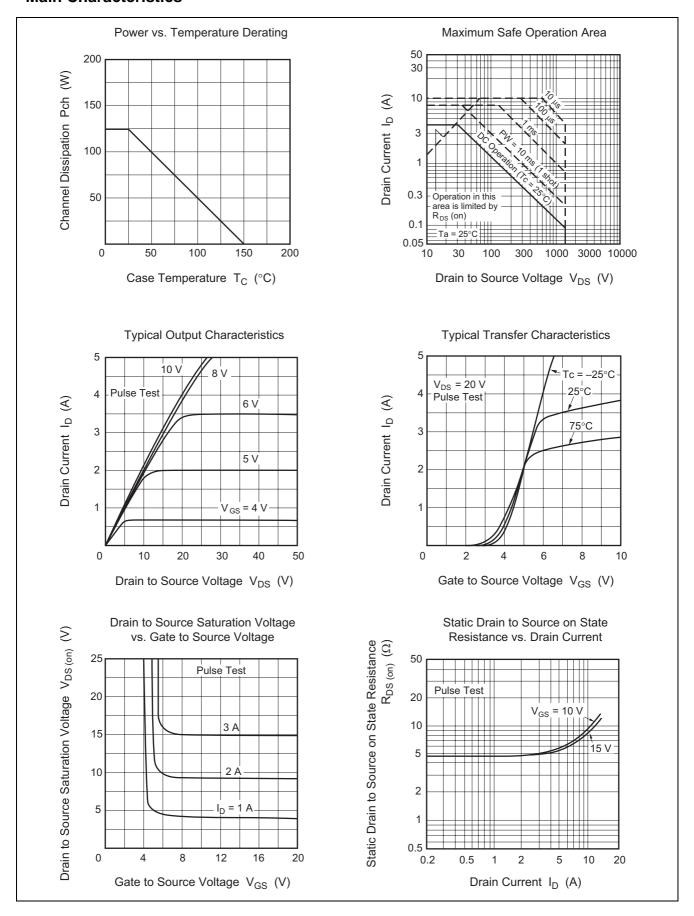
Electrical Characteristics

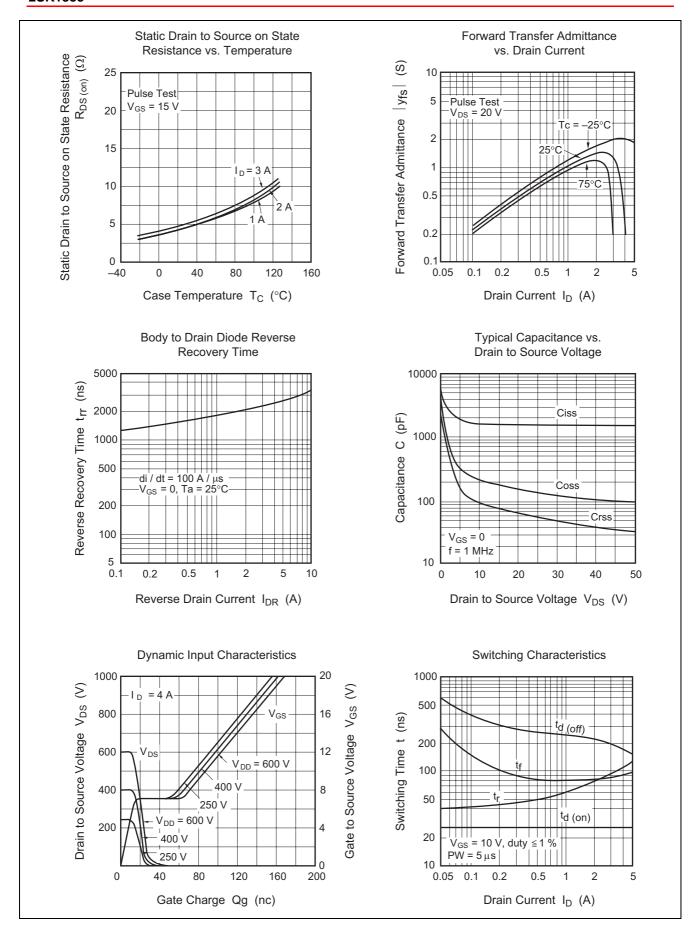
 $(Ta = 25^{\circ}C)$

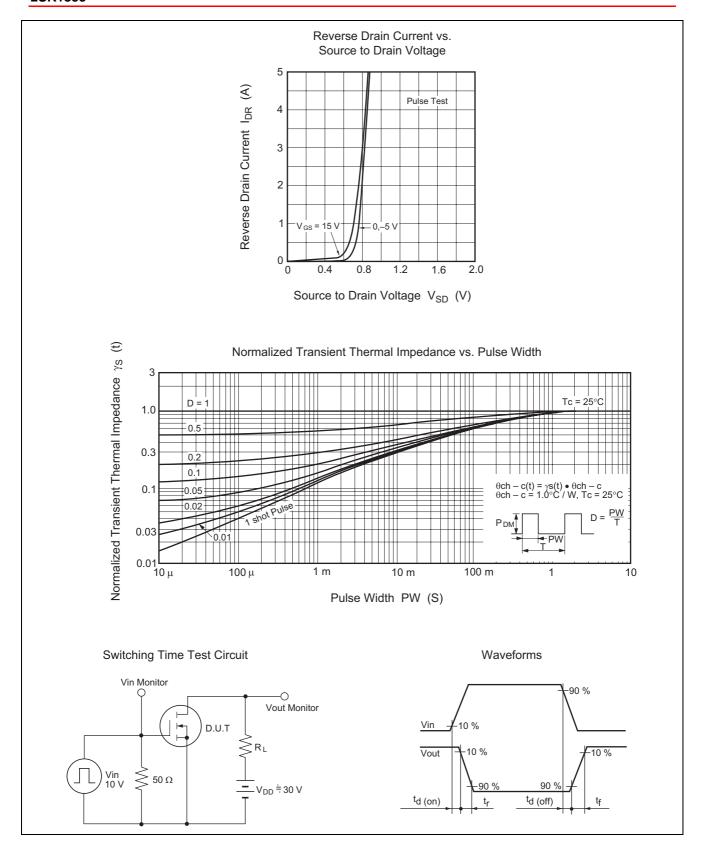
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	V _{(BR)DSS}	1500	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source leak current	I _{GSS}	_	_	±1	μΑ	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I _{DSS}	_	_	500	μΑ	$V_{DS} = 1200 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	2.0	_	4.0	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Static drain to source on state	R _{DS(on)}	_	4.6	7.0	Ω	$I_D = 2 \text{ A}, V_{GS} = 15 \text{ V}^{\text{Note 3}}$
resistance						
Forward transfer admittance	y _{fs}	0.9	1.4	_	S	$I_D = 2 \text{ A}, V_{DS} = 20 \text{ V}^{\text{Note 3}}$
Input capacitance	Ciss	_	1700	_	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0,$
Output capacitance	Coss	_	230	_	pF	f = 1 MHz
Reverse transfer capacitance	Crss	_	100	_	pF	
Turn-on delay time	t _{d(on)}	_	25	_	ns	$I_D = 2A, V_{GS} = 10 V,$
Rise time	t _r	_	80	_	ns	$R_L = 15 \Omega$
Turn-off delay time	$t_{d(off)}$	_	230	_	ns	
Fall time	t _f	_	80	_	ns	
Body to drain diode forward voltage	V_{DF}	_	0.85	_	V	$I_F = 4 \text{ A}, V_{GS} = 0$
Body to drain diode reverse	t _{rr}	_	2500	_	ns	$I_F = 4 \text{ A}, V_{GS} = 0,$
recovery time						$di_F/dt = 100 A/\mu s$

Note: 3. Pulse Test

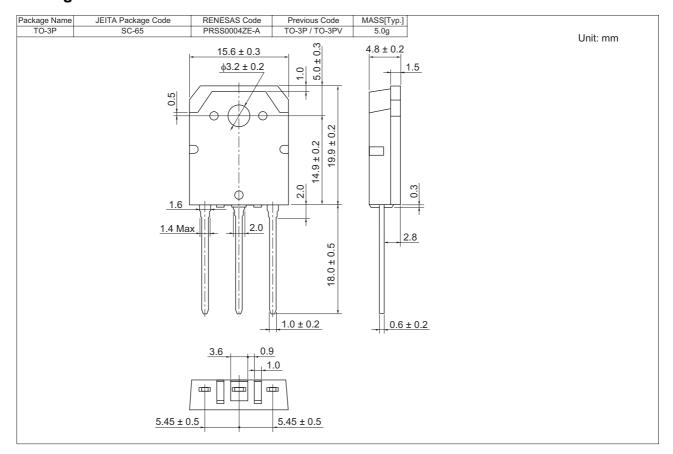
Main Characteristics







Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
2SK1835-E	360 pcs	Box (Tube)

Renesas Technology Corp. sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

- Renesas lechnology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan Notes:

 1. This document is provided for reference purposes only so that Renesas customers may select the appropriate Renesas products for their use. Renesas neither makes warrantes or representations with respect to the accuracy or completeness of the information in this document nor grants any license to any intellectual property girbs to any other rights of representations with respect to the information in this document in this document of the purpose of the respect of the information in this document in the product data, diagrams, charts, programs, algorithms, and application circuit examples.

 3. You should not use the products of the technology described in this document for the purpose of military use. When exporting the products or technology described herein, you should follow the applicable export control laws and regulations, and procedures required by such laws and regulations, and procedures required to change without any plan protein. Before purchasing or using any Renesas products listed in this document, in the development is satisfied. The procedure is such as the development of the dev



RENESAS SALES OFFICES

http://www.renesas.com

Refer to "http://www.renesas.com/en/network" for the latest and detailed information.

Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology (Shanghai) Co., Ltd.
Unit 204, 205, AZIACenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120 Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7858/7898

Renesas Technology Hong Kong Ltd.
7th Floor, North Tower, World Finance Centre, Harbour City, Canton Road, Tsimshatsui, Kowloon, Hong Kong Tel: <852> 2265-6688, Fax: <852> 2377-3473

Renesas Technology Taiwan Co., Ltd. 10th Floor, No.99, Fushing North Road, Taipei, Taiwan Tel: <886> (2) 2715-2888, Fax: <886> (2) 3518-3399

Renesas Technology Singapore Pte. Ltd.

1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd. Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510